

John Niroula is currently a technology architect at GlobalFoundries in the gfLABs organization where he helps technology development and pathfinding efforts focused on RF GaN-on-Silicon platforms for next-generation high-volume applications. His work spans semiconductor process integration, device engineering, technology pathfinding, funding capture and external research collaborations.

John received his Ph.D. in Electrical Engineering from the Massachusetts Institute of Technology (MIT), where his research focused on the design, fabrication, characterization, and modeling of thermally hardened RF GaN electronics capable of operation beyond 500°C. His work demonstrated record-performance high-temperature GaN transistors and contributed to the understanding of GaN device physics under extreme operating conditions. Prior to joining GlobalFoundries, he held engineering and research positions at MIT, Northrop Grumman, Analog Devices, Sandia National Laboratories, the Air Force Research Laboratory, and the Jet Propulsion Laboratory.

An active contributor to the semiconductor research community, John has authored more than 30 technical publications in the field and holds 3 patents.